





#### 100V PNP MEDIUM POWER TRANSISTOR IN SOT223

#### **Features**

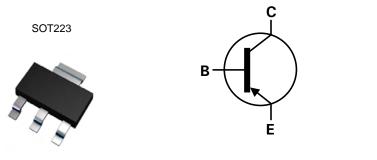
- $BV_{CEO} > -100V$
- I<sub>C</sub> = -5A high Continuous Collector Current
- I<sub>CM</sub> = -10A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -90mV @ -1A
- $R_{SAT} = 60m\Omega$  for a low equivalent On-Resistance
- hFE specified up to -10A for a high gain hold up
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

# **Mechanical Data**

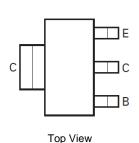
- Case: SOT223
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (approximate)

#### **Applications**

- Motor driving
- Line switching
- High side switches
- Subscriber line interface cards (SLIC)







Pin-Out

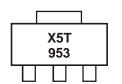
### Ordering Information (Notes 4 & 5)

Top View

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZX5T953GTA	AEC-Q101	X5T953	7	12	1,000
ZX5T953GQTA	Automotive	X5T953	7	12	1,000

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

### **Marking Information**



X5T953 = Product type Marking Code





# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-140	V
Collector-Emitter Voltage	$V_{CEO}$	-100	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-5	Α
Peak Pulse Current	I <sub>CM</sub>	-10	Α

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	Б	3.0 24	W
Linear derating factor	(Note 7)	$P_{D}$	1.6 12.8	mW /°C
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	42	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	78	°C/W
Thermal Resistance Junction to Lead (Note 8)		$R_{ heta JL}$	10.48	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

#### ESD Ratings (Note 9)

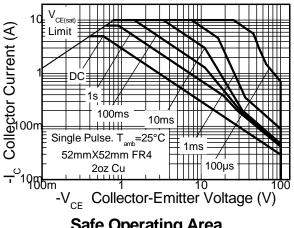
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

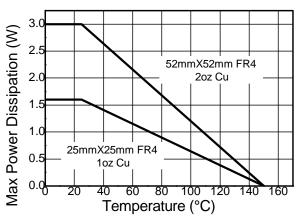
Notes:

For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
Same as note (6), except the device is surface mounted on 25mm x 25mm with 1oz copper.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



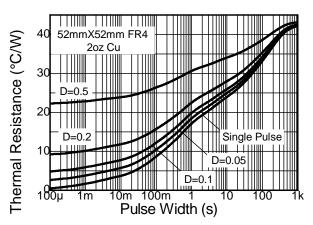
#### **Thermal Characteristics and Derating Information**

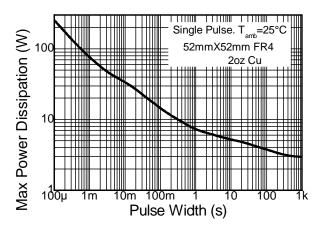




# **Safe Operating Area**

**Derating Curve** 





**Transient Thermal Impedance** 

**Pulse Power Dissipation** 





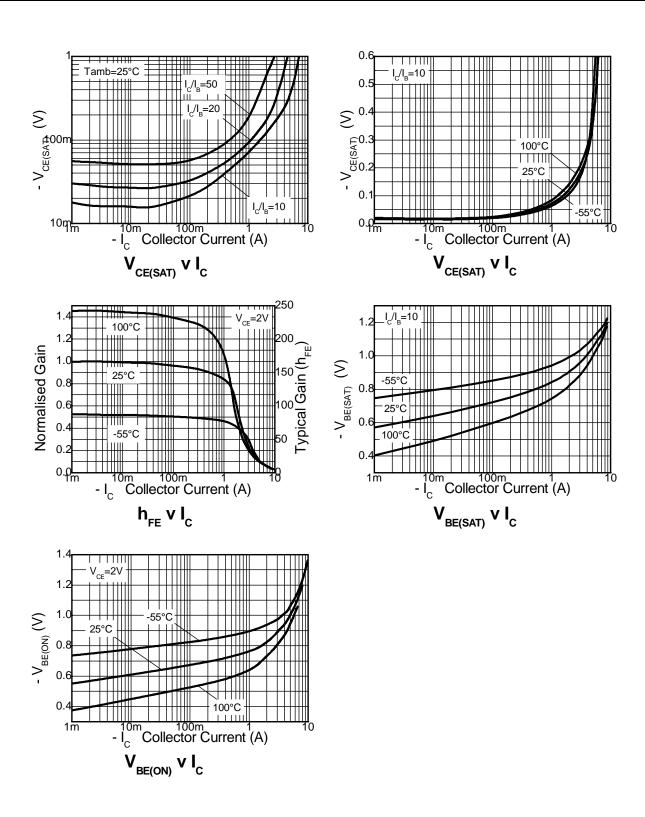
#### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-140	-160	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	-140	-160	-	V	$I_C = -1\mu A$ , RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	-100	-115	-	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.1	-	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	Ісво	-	<1 -	-20 -0.5	nΑ μΑ	V <sub>CB</sub> = -100V V <sub>CB</sub> = -100V, T <sub>A</sub> = +100°C
Collector-Emitter Cutoff Current	l <sub>CER</sub> R ≤ 1kΩ	-	<1 -	-20 -0.5	nΑ μΑ	V <sub>CB</sub> = -100V V <sub>CB</sub> = -100V, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	-	<1	-10	nA	$V_{EB} = -6V$
		100	250	-	-	$I_{C} = -10 \text{mA}, V_{CE} = -1 \text{V}$
		100	200	300		$I_{C} = -1A, V_{CE} = -1V$
Static Forward Current Transfer Ratio (Note 10)	h <sub>FE</sub>	25	50	-		I <sub>C</sub> = -3A, V <sub>CE</sub> = -1V
		15	30	-		I <sub>C</sub> = -4A, V <sub>CE</sub> = -1V
		-	5	-		I <sub>C</sub> = -10A, V <sub>CE</sub> = -1V
	V <sub>CE(sat)</sub>	-	-20	-30		$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Collector Emitter Seturation Voltage (Note 10)		-	-70	-90	mV	$I_C = -1A$ , $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 10)		-	-120	-150	IIIV	$I_C = -2A$ , $I_B = -200mA$
		-	-240	-340		$I_C = -4A$ , $I_B = -400mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	-	-985	-1100	mV	$I_C = -4A$ , $I_B = -400$ mV
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	-	-920	-1050	mV	$I_{C} = -4A$ , $V_{CE} = -2V$
Output Capacitance (Note 10)	C <sub>obo</sub>	-	42	-	pF	V <sub>CB</sub> = -10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	-	125	-	MHz	$V_{CE} = -10V, I_{C} = -100mA$ f = 50MHz
Switching Time	t <sub>on</sub>	-	42	-	ns	$V_{CC} = -10V, I_{C} = -1A$
Switching Time	t <sub>off</sub>	-	540	-	115	$I_{B1} = I_{B2} = -100 \text{mA}$

Notes: 10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%



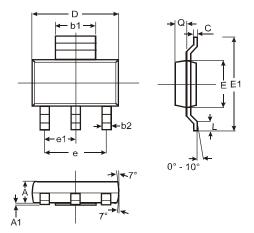
# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





# **Package Outline Dimensions**

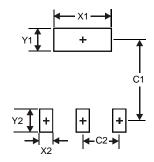
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1		_	2.30		
L	0.85	1.05	0.95		
ø	0.84	0.94	0.89		
All Dimensions in mm					

#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3





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